

GF300SD120T2ZH

IGBT Module

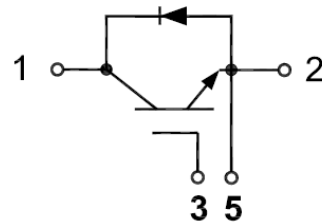
Features:

- Short Circuit Rated > 10 μ s
- Low Saturation Voltage: $V_{CE(sat)} = 3.10V @ I_C = 300A, T_C=25^\circ C$
- Low Switching Loss
- 100% RBSOA Tested ($2 \times I_C$)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



Applications:

- Motor Drives
- Induction Heating
- Ultrasonic Device
- High Frequency Switching Application



IGBT, Inverter

Maximum Rated Values ($T_C=25^\circ C$ unless otherwise specified)

V_{CES}	Collector-Emitter Blocking Voltage		1200	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Continuous Collector Current	$T_C = 80^\circ C$	300	A
		$T_C = 25^\circ C$	520	A
$I_{CM(1)}$	Peak Collector Current Repetitive	$T_J = 150^\circ C$	600	A
t_{SC}	Short Circuit Withstand Time		>10	μs
P_D	Maximum Power Dissipation per IGBT	$T_C = 25^\circ C$ $T_{Jmax} = 150^\circ C$	2500	W

Electrical Characteristics of IGBT ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Static Characteristics

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C = 3 \text{ mA}$, $V_{CE} = V_{GE}$	5.0	5.4	6.0	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 300\text{A}$, $V_{GE} = 15\text{V}$	$T_J = 25^{\circ}\text{C}$	3.10	3.40	V
			$T_J = 125^{\circ}\text{C}$	3.40		V
I_{CES}	Collector-Emitter Leakage Current	$V_{GE} = 0\text{V}$, $V_{CE} = V_{CES}$, $T_J = 25^{\circ}\text{C}$			5	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE} = \pm 20\text{V}$, $V_{CE} = 0\text{V}$, $T_J = 25^{\circ}\text{C}$			400	nA
C_{ies}	Input Capacitance	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		38.0		nF
C_{oes}	Output capacitance			2.72		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC} = 600\text{V}$, $I_C = 300\text{A}$, $R_G = 6.2\Omega$, $V_{GE} = \pm 15\text{V}$, Inductive Load	$T_J = 25^{\circ}\text{C}$	280		ns
			$T_J = 125^{\circ}\text{C}$	260		
t_r	Rise Time		$T_J = 25^{\circ}\text{C}$	170		ns
			$T_J = 125^{\circ}\text{C}$	170		
$t_{d(off)}$	Turn-off Delay Time		$T_J = 25^{\circ}\text{C}$	700		ns
			$T_J = 125^{\circ}\text{C}$	750		
t_f	Fall Time		$T_J = 25^{\circ}\text{C}$	125		ns
			$T_J = 125^{\circ}\text{C}$	150		
E_{on}	Turn-on Switching Loss		$T_J = 25^{\circ}\text{C}$	16.8		mJ
			$T_J = 125^{\circ}\text{C}$	22.3		
E_{off}	Turn-off Switching Loss	$T_J = 25^{\circ}\text{C}$	11.4		mJ	
		$T_J = 125^{\circ}\text{C}$	16.2			
Q_g	Total Gate Charge	$T_J = 25^{\circ}\text{C}$	3780		nC	
RBSOA	Reverse Bias Safe Operation Area	$I_C=600\text{A}$, $V_{CC}=1050\text{V}$, $V_p=1200\text{V}$, $R_g = 6.2\Omega$, $V_{GE}=\pm 15\text{V}$ to 0V , $T_J = 150^{\circ}\text{C}$	Trapezoid			
SCSOA	Short Circuit Safe Operation Area	$V_{CC} = 600\text{V}$, $V_{GE} = 15\text{V}$, $T_J = 150^{\circ}\text{C}$	10		μs	
$R_{\theta JC}$	IGBT Thermal Resistance: Junction-To-Case			0.051	$^{\circ}\text{C/W}$	

Diode, Inverter
Maximum Rated Values ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	300	A
I_{FM}	Repetitive Peak Forward Current	600	A

Electrical Characteristics of FWD ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Description	Conditions	Min	Typ	Max	Unit
V_{FM}	Forward Voltage	$I_F = 300\text{A}$	$T_J = 25^{\circ}\text{C}$	2.40		V
			$T_J = 125^{\circ}\text{C}$	2.60		
I_{rr}	Peak Reverse Recovery Current		$T_J = 25^{\circ}\text{C}$	110		A
			$T_J = 125^{\circ}\text{C}$	160		
Q_{rr}	Reverse Recovery Charge	$I_F = 300\text{A}$, $di/dt = 1700\text{A}/\mu\text{s}$, $V_{rr} = 600\text{V}$, $V_{GE} = -15\text{V}$	$T_J = 25^{\circ}\text{C}$	11.6		μC
			$T_J = 125^{\circ}\text{C}$	18.7		
E_{rec}	Reverse Recovery Energy		$T_J = 25^{\circ}\text{C}$	5.3		mJ
			$T_J = 125^{\circ}\text{C}$	12.2		
$R_{\theta JC}$	Diode Thermal Resistance: Junction-To-Case			0.164		$^{\circ}\text{C}/\text{W}$

Module

Symbol	Description	Min	Typ	Max	Unit
V_{iso}	Isolation Voltage (All Terminals Shorted)	$f = 50\text{Hz}$, 1minute	2500		V
T_J	Maximum Junction Temperature			150	$^{\circ}\text{C}$
T_{JOP}	Maximum Operating Junction Temperature Range	-40		+150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-40		+125	$^{\circ}\text{C}$
CTI	Comparative Tracking Index	200			V
$R_{\theta CS}$	Case-To-Sink Thermally (Conductive Grease Applied)		0.03		$^{\circ}\text{C}/\text{W}$
M	Power Terminals Screw: M6	3.0		5.0	N·m
M	Mounting Screw: M6	4.0		6.0	N·m
G	Weight		310		g

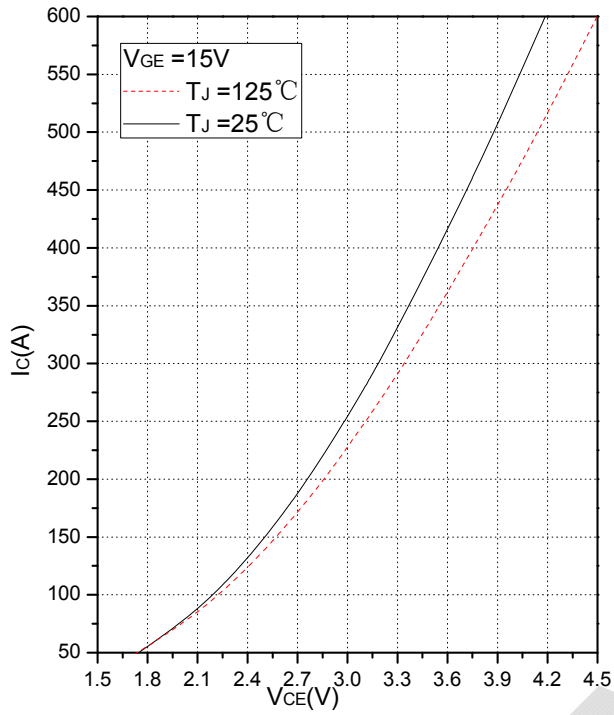


Fig.1 Typical Saturation Voltage Characteristics

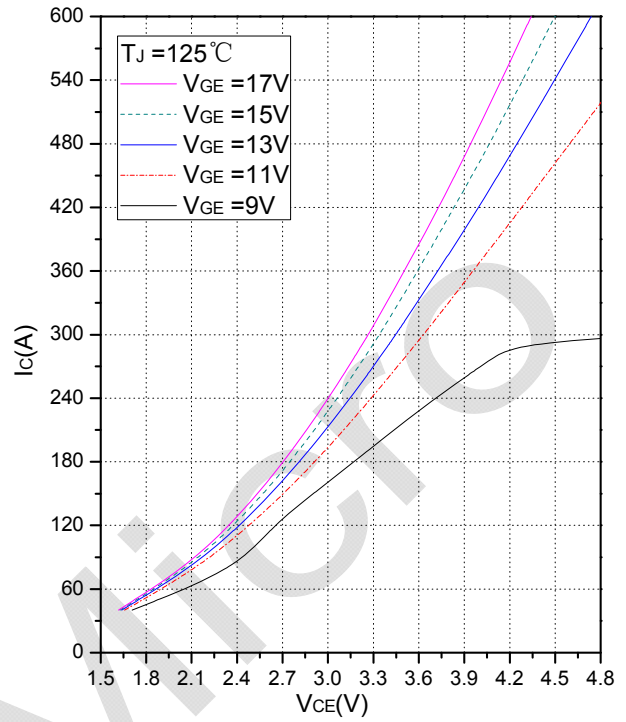


Fig.2 Typical Output Characteristics

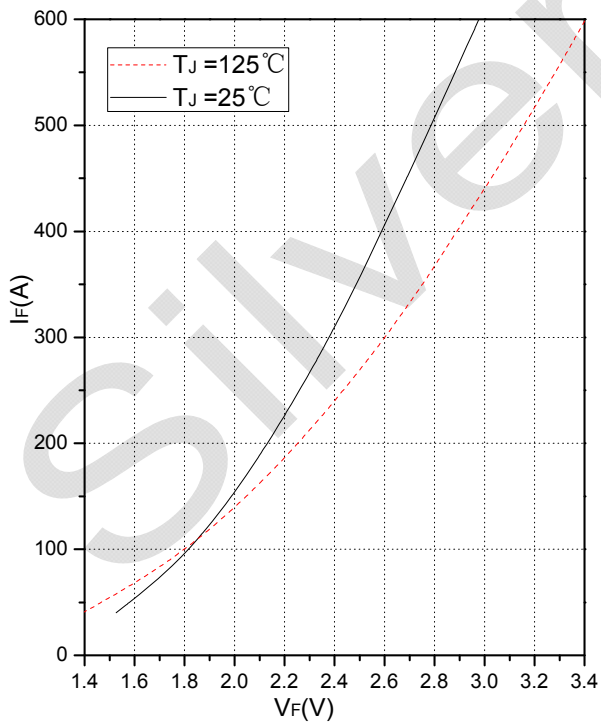


Fig.3 Forward Characteristics of FWD

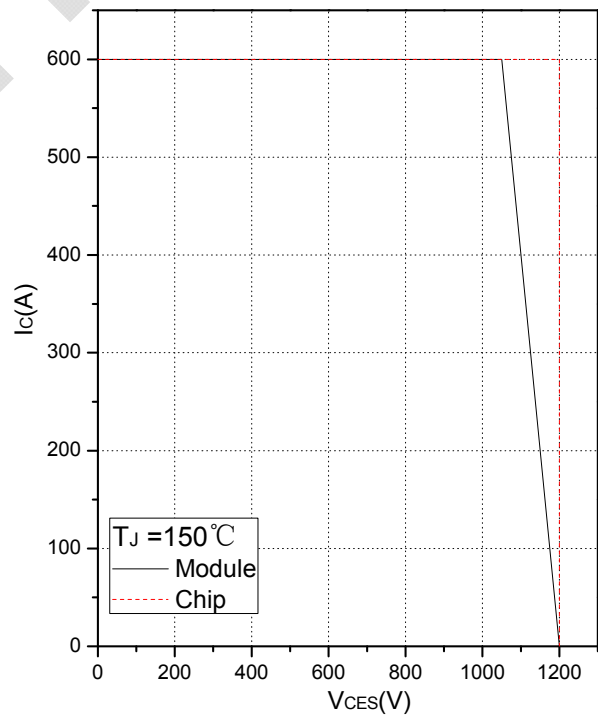


Fig.4 Reverse Bias Safe Operation Area (RBSOA)

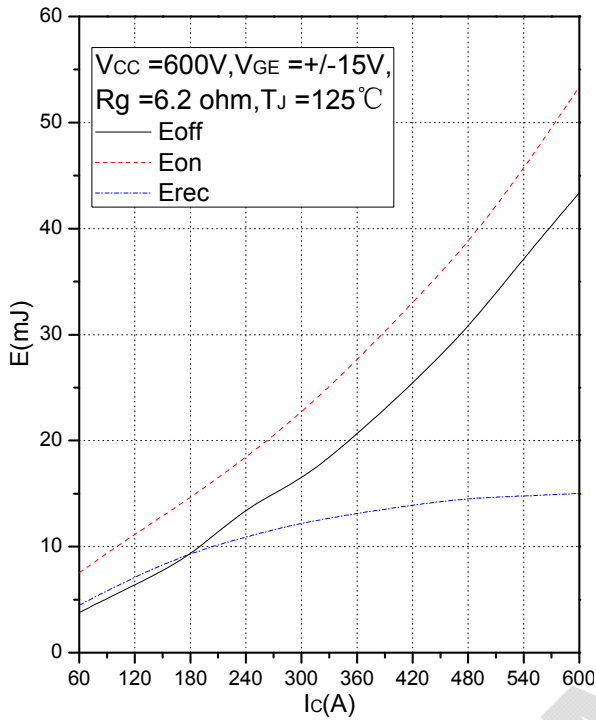


Fig.5 Typical Switching Loss vs. Collector Current

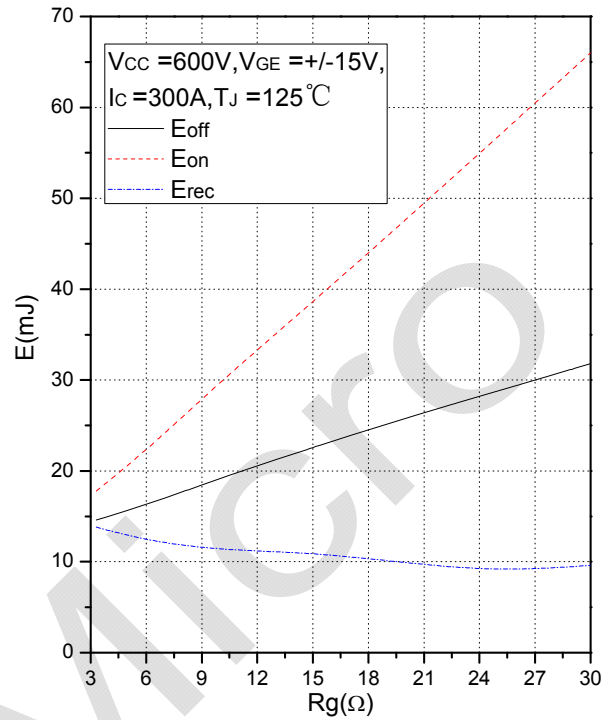


Fig.6 Typical Switching Loss vs. Gate Resistance

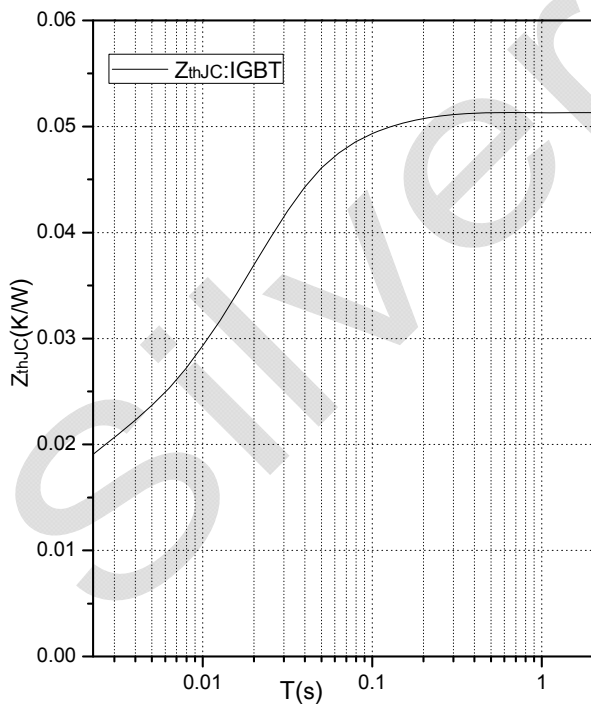


Fig.7 Transient Thermal Impedance (IGBT)

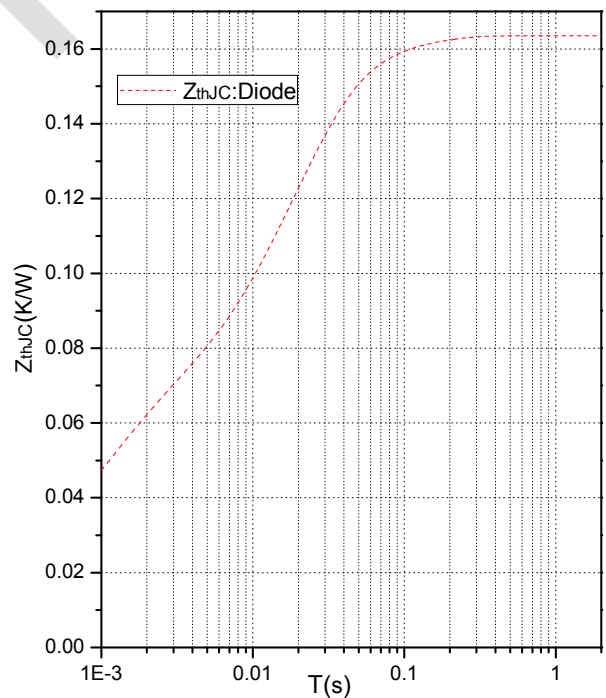
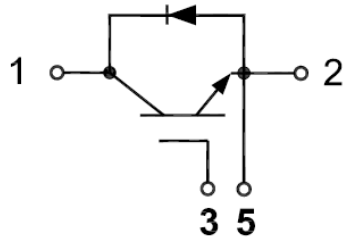
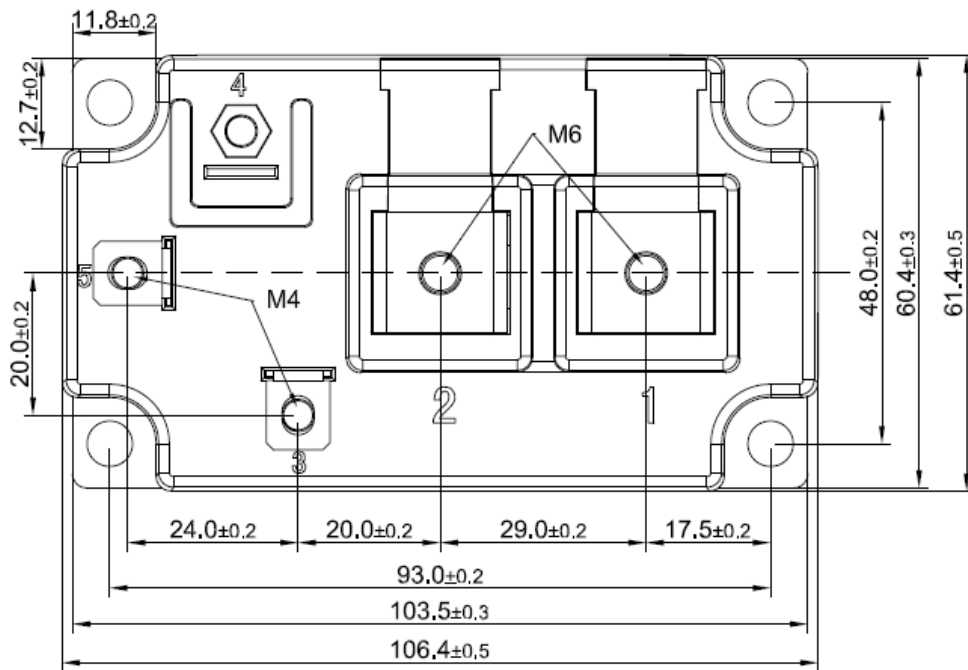
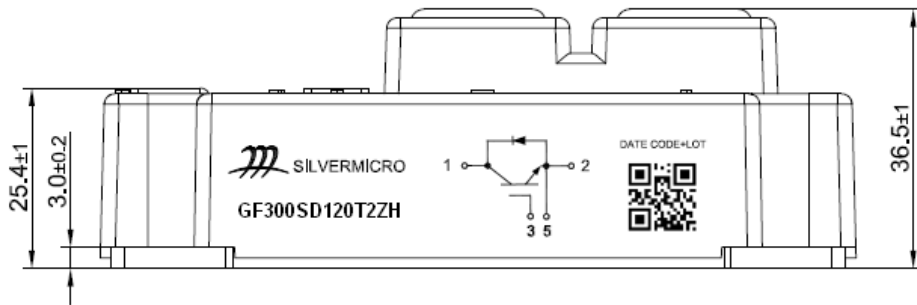


Fig.8 Transient Thermal Impedance (Diode)

Internal Circuit:



Package Outline (Unit: mm):





Announcement

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